

TWO-WIRE AUTOMOTIVE HALL EFFECT UNIPOLAR / LATCH SWITCHES

Description

The DIODES[™] AH3231Q-AH3234Q/AH3270Q-AH3272Q are high voltage, high sensitivity, two-wire Hall Effect Unipolar/Latch switch ICs with automotive-compliant AEC-Q100 qualification; designed for position and proximity sensing in automotive applications, such as seat and seatbelt buckle, transmission actuator, gear position, wiper, door/trunk closure, etc.

To support a wide range of demanding applications, the design is optimized to operate over a supply range of 2.7V to 27V. These features include a chopper-stabilized architecture and an internal bandgap regulator to provide temperature compensated supply for internal circuits. For robustness and protection, the device has built-in reverse blocking diode with a Zener clamp on the supply.

The built-in thermal protection also shuts down the chip if temperature rises to an abnormal value. This will automatically restart the chip once the junction temperature drops below the safe value.

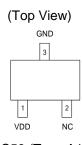
For the AH3231Q, AH3232Q, AH3233Q, and AH3234Q two-wire unipolar switches: when the flux density (south pole) exceeds B_{OP} , the supply current state is turned on (low or high). The output is held until a magnetic flux density falls below B_{RP} , causing output current to be turned off.

For the AH3270Q, AH3271Q, and AH3272Q two-wire latch switches: when the magnetic flux density is larger than B_{OP} , output current is turned on (high). The output state is held until a magnetic flux density reversal falls below B_{RP} , causing output current to be turned off (low).

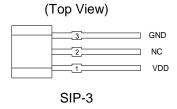
Features and Performance

- Unipolar: AH3231Q, AH3232Q, AH3233Q, AH3234Q
 Latch: AH3270Q, AH3271Q, AH3272Q
- Output Polarity:
 - Direct: AH3232Q, AH3233Q
 - Inverted: AH3231Q, AH3234Q
- Wide Supply Voltage Operation: 2.7V to 27V
- Temperature Coefficient -1100ppm/°C (AH3232Q, AH3233Q, AH3234Q)
- Chopper Stabilized Design Provides:
 - Superior Temperature Stability
 - Minimal Switch Point Drift
 - Enhanced Immunity to Stress
- Battery polarity reverse connection protection
- Transient Spike Voltage Protection
- Overtemperature Shut Down and Auto-Restart
- UVLO Protection
- High ESD Rating: HBM = 8kV, CDM = 1kV
- Temperature Range:-40°C to +150°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1, 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The AH3231Q-AH3234Q/AH3270Q-AH3272Q are suitable for automotive applications requiring specific change control; these parts are AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. <u>https://www.diodes.com/quality/product-definitions/</u>

Pin Assignments



SC59 (Type A1)



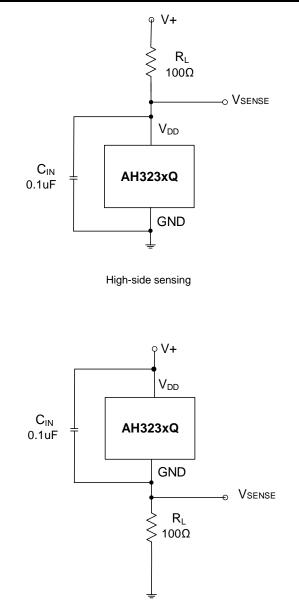
Applications

- Position and proximity sensing in automotive applications
- Seat positioning
- Seatbelt buckles
- Wiper positioning
- Window lifters
- Gear selection positioning

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and<1000ppm antimony compounds.



Typical Applications Circuit





Note: 4. A 100nF or larger decoupling capacitor (CIN) between VDD and GND pins is needed for power stabilization and to strengthen noise immunity; CIN needs to be as close to IC as possible. Typical RL value is 100Ω. Larger or additional series resistor is recommended if there are disturbances on VDD.

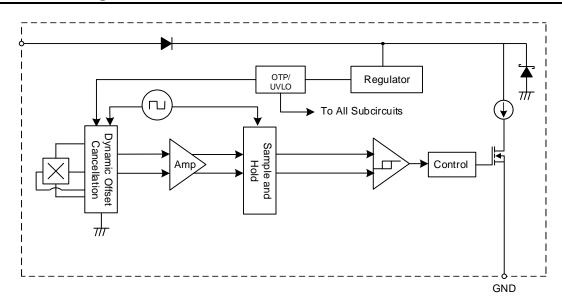
Pin Descriptions

Package: SC59 and SIP-3 (Ammo Pack and Bulk Pack)

Pin Number	Pin Name	Function
1	V _{DD}	Supply voltage input
2	NC	No connection; can be connected to VDD, GND, or left open.
3	GND	Ground



Functional Block Diagram



Absolute Maximum Ratings (Note 5) (@ T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
V _{DD} (Note 6)	Supply Voltage	32	V
V _{DDR} (Note 6)	Reverse Supply Voltage	-32	V
В	Magnetic Flux Density	Unlimited	Gauss
T _{J_MAX}	Maximum Junction Temperature	180	°C
Ts	Storage Temperature	-55~180	°C
ESD (HBM)	ESD (Human Body Model)	8000	V
ESD (CDM)	ESD (Charged Device Model)	1000	V

Notes: 5. Stresses greater than the "Absolute Maximum Ratings" specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

6. Should not be exceeded the maximum junction temperature and maximum duration of 500ms.

Recommended Operating Conditions (@ T_A = -40°C to +150°C, T_J = -40°C to +165°C unless otherwise specified.)

Symbol	Parameter	Min	Мах	Unit
VDD	Supply Voltage, between V _{DD} and GND pins	2.7	27	V
T _{OP}	Operating Ambient Temperature	-40	150	°C



Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{DD}	Supply voltage (Note 8)	-	2.7	12	27	V
I _{OFF} (1)	Supply current off state	V _{DD} =2.7 to 27 V (AH3270Q, AH3272Q)	2	3.3	5	mA
I _{OFF} (2)	Supply current off state	V _{DD} = 2.7 to 27 V (AH3231Q, AH3232Q, AH3233Q, AH3234Q, AH3271Q)	5	6	6.9	mA
I _{ON}	Supply current on state	V _{DD} = 2.7 to 27 V	12	14.5	17	mA
VUVLO	Under voltage lockout threshold	Voltage dropping	-	2.2	2.7	V
t _{UVLO}	Under-voltage lockout reaction time	-	-	10	-	μs
I _{DDR}	Reverse supply current	V_{DD} = -18V , T_A = -40°C to +150°C	-1.5	-	-	mA
T _{TP}	Thermal protection threshold	Junction temperature	-	190	-	°C
T _{TPR}	Thermal protection release threshold	Junction temperature	-	180	-	°C
F _M	Maximum magnet switching frequency	$B > 3^*B_{OP}$, alternative square magnet field	30	50	-	kHz
Fc	Chopping frequency	-	-	1000	-	kHz
T _{PON}	Power on delay time (Note 9)	$B > B_{OP}+10GS$	-	28	40	μs
TD	Response delay time (Note 10)	B > 3*B _{OP}	-	7	-	μs
T _{RF}	Current rise/fall time	V_{DD} = 12V, No bypass capacitor, C_{LOAD} = 50pF to GND	0.1	0.3	1	μs
POS	Power-up state (Notes 9, 11)	t > T _{PON} (max), V _{DD} slew rate > 1V/µs	-	IOFF	-	-
-	Output jitter	B≥3*B _{OPMAX} 1000 successive square wave switching under 1KHz.	-	±3.3	-	μs

 Typical values are defined at TA = +25°C, VDD = 12V. Maximum and minimum values over the operating temperature range are not tested in production but guaranteed by design, process control and characterization.
 VDD is the voltage between the VDD pin and the GND pin.
 When power is initially turned on, V_{DD} must be operated in the correct voltage range to guarantee proper magnetic field sampling, output supply current state level is valid after the start up time of 28µs from V_{DD} higher than 2.7V. Guaranteed by design.
 Time delayed from the meansitie threshold to the output rise or fall. Notes:

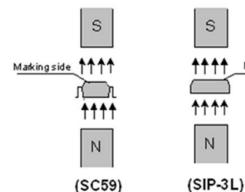
10. Time delayed from the magnetic threshold reached to the output rise or fall.

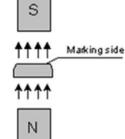
11. t > T_{PON} and $B_{RP} < B < B_{OP}$.



Magnetic Characteristics (Notes 12,13) (T_A = -40°C to +150°C, T_J = -40°C to +165°C, V_{DD}= 2.7V to 27V, unless otherwise specified)

Part Name	Test Condition		erating P _{OP} (Gaus			elease Po _{RP} (Gaus		Temperature Coefficient (ppm/°C)	I _{OFF} (mA)	Active Pole	Output Polarity
		Min	Тур	Max	Min	Тур	Max	Тур	Тур		
AH3231Q	T _A =25°C	65	90	120	45	70	100	0	6	South	Inverted
AU2210	T _A =-40~150°C	55	90	135	35	70	115		0	South	Inventeu
AH3232Q	T _A =25°C	40	60	80	20	40	60	1100	6	South	Direct
AUSZSZÓ	T _A =-40~150°C	30	60	90	10	40	70	-1100	0	South	
41122220	T _A =25°C	27	45	63	10	28	46	-1100	6	Courth	Direct
AH3233Q	T _A =-40~150°C	20	45	70	3	28	53			South	
41122240	T _A =25°C	27	45	63	10	28	46	1100	G	Couth	Inverted
AH3234Q	T _A =-40~150°C	20	45	70	3	28	53	-1100	6	South	Inverted
AH3270Q	T _A =25°C	8	18	28	-28	-18	-8	0	3.3		Direct
AH3270Q	T _A =-40~150°C	3	18	33	-33	-18	-3	0	3.3	South	
41100740	T _A =25°C	8	18	28	-28	-18	-8	0	6	Courth	Direct
AH3271Q	T _A =-40~150°C	3	18	33	-33	-18	-3		6	South	Direct
41100700	T _A =25°C	15	30	45	-45	-30	-15	0	3.3 South	Courth	
AH3272Q	T _A =-40~150°C	10	30	50	-50	-30	-10	0		South	Direct





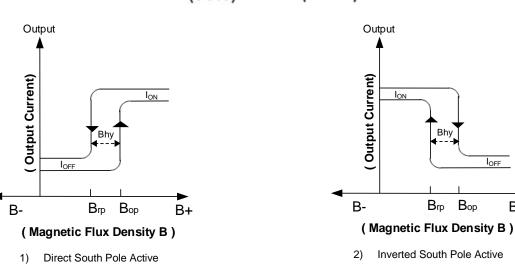
Bhy

Brp

Bop

I_{OFF}

B+

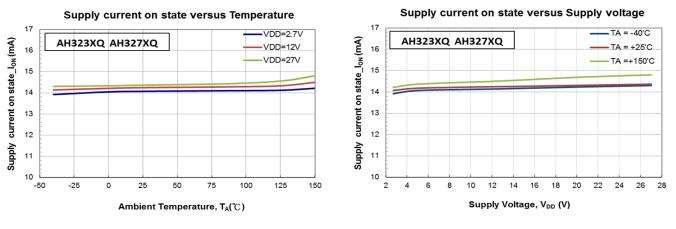


12. Positive x-axis direction indicates the South Pole approaching the part marking surface of SIP3 and SC59 i.e. increasing south pole magnetic field Notes: 12. F Using X-axis unection indicates the South Pole approaching the part marking surface of SIP3 and SC59 i.e. increasing south pole magnetic field strength to the sensor; reversing direction x-axis toward 0 means the decreasing south magnetic field strength to the sensor. Negative x-axis indicates north pole magnetic field to the part marking surface.
 13. Typical values are defined at T_A = +25°C, V_{DD} = 12V. Maximum and minimum values over the operating temperature range is not tested in production but design process control and characterization.

but guaranteed by design, process control and characterization.

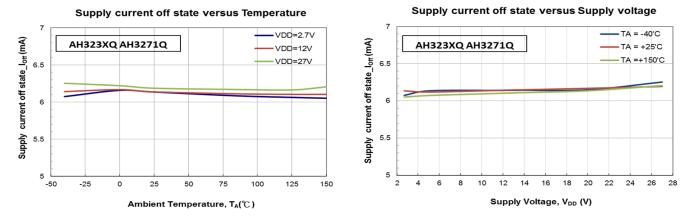


Typical Operating Characteristics

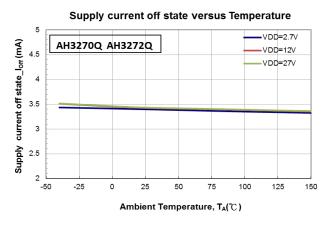


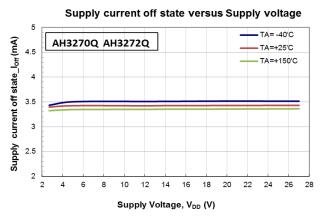
AH323XQ_AH327XQ Supply Current ON, IoN Performance

AH323XQ_AH3271Q Supply Current OFF, IOFF(1) Performance



AH3270Q_AH3272Q Supply Current OFF, IOFF(2) Performance







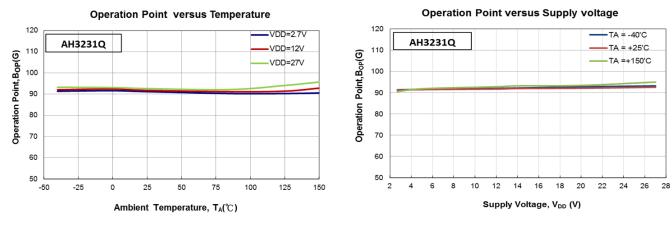
45 └ -50

-25

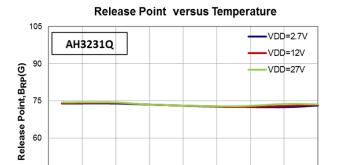
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Typical Operating Characteristics (continued)



AH3231Q Magnetic Characteristics Performance



50

Ambient Temperature, $T_A(^{\circ}C)$

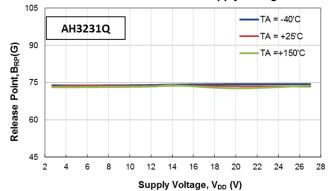
75

100

125

150

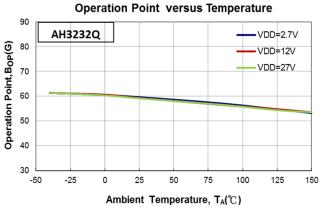
Release Point versus Supply voltage



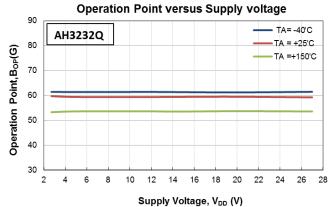
Switch Point Hysteresis versus Temperature Switch Point Hysteresis versus Supply voltage 40 40 Switch Point Hysteresis, B_{HY}(G) -TA = -40'C AH3231Q AH3231Q VDD=2.7V 35 Switch Point Hysteresis, B_{HY}(G) 35 - TA = +25'C VDD=12V 30 30 -TA =+150'C VDD=27V 25 25 20 20 15 15 10 10 5 5 -50 -25 0 25 50 75 100 125 150 2 4 6 8 10 12 14 16 18 20 22 24 26 28 Supply Voltage, V_{DD} (V) Ambient Temperature, T_A(℃)



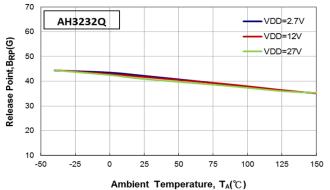
Typical Operating Characteristics (continued)



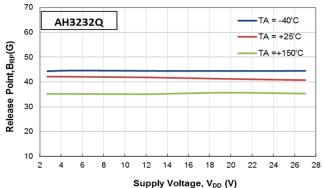
AH3232Q Magnetic Characteristics Performance

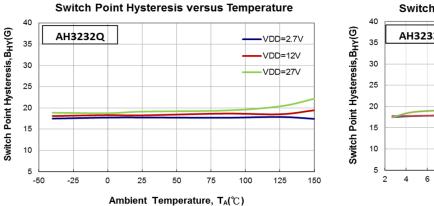


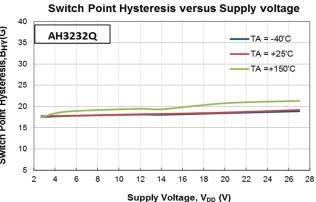
Release Point versus Temperature



Release Point versus Supply voltage

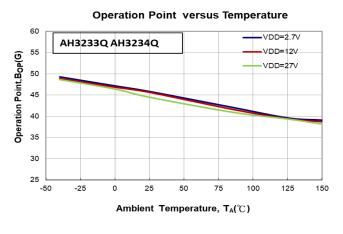




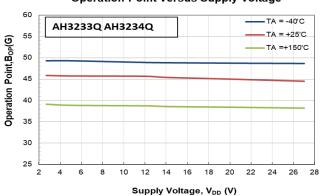




Typical Operating Characteristics (continued)

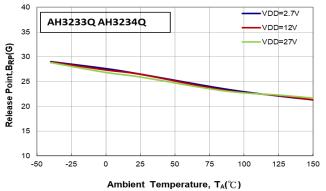


AH3233Q_AH3234Q Magnetic Characteristics Performance

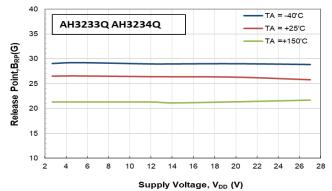


Operation Point versus Supply voltage

Release Point versus Temperature



Release Point versus Supply voltage

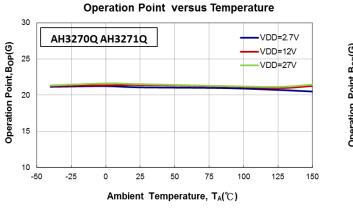


Switch Point Hysteresis versus Temperature 35 -VDD=2.7V AH3233Q AH3234Q Switch Point Hysteresis, B_{HY}(G) VDD=12V 30 VDD=27V 25 20 15 10 5 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, $T_A(^{\circ}C)$

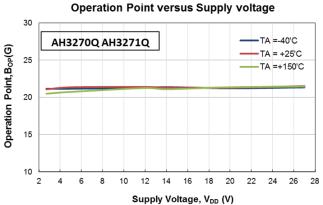
Switch Point Hysteresis versus Supply voltage 35 - TA = -40'C Switch Point Hysteresis, B_{HY}(G) AH3233Q AH3234Q - TA = +25'C 30 TA =+150'C 25 20 15 10 5 18 20 22 24 26 2 4 6 8 10 12 14 16 28 Supply Voltage, V_{DD} (V)



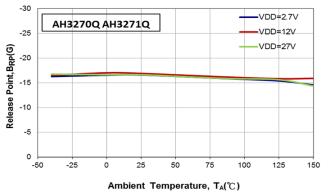
Typical Operating Characteristics (continued)



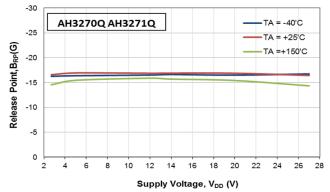
AH3270Q_AH3271Q Magnetic Characteristics Performance



Release Point versus Temperature

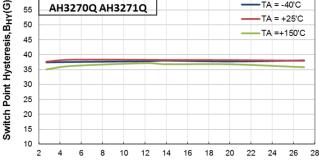


Release Point versus Supply voltage



Switch Point Hysteresis versus Temperature 60 VDD=2.7V Switch Point Hysteresis, B_{HY}(G) AH3270Q AH3271Q 55 VDD=12V 50 -VDD=27V 45 40 35 30 25 20 15 10 -50 -25 25 50 75 100 125 150 0 Ambient Temperature, T_A(℃)

Switch Point Hysteresis versus Supply voltage 60 -TA = -40'C AH3270Q AH3271Q 55 -TA = +25'C 50 -TA =+150'C 45 40

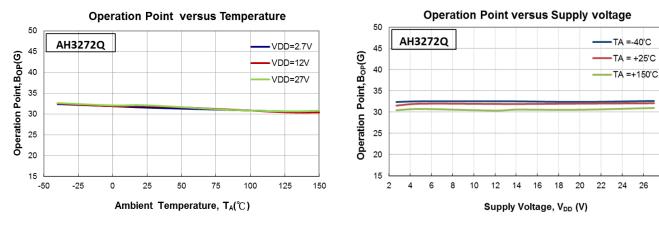


Supply Voltage, V_{DD} (V)



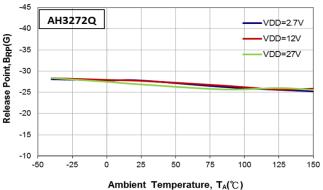
26 28

Typical Operating Characteristics (continued)

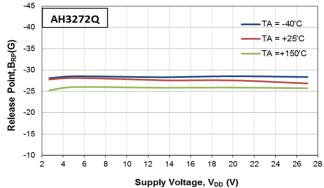


AH3272Q Magnetic Characteristics Performance

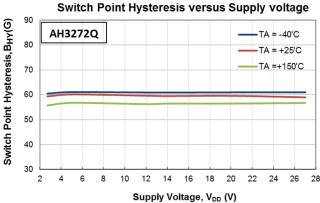
Release Point versus Temperature



Release Point versus Supply voltage



Switch Point Hysteresis versus Temperature 90 Switch Point Hysteresis, B_{HY}(G) AH3272Q VDD=2.7V 80 VDD=12V VDD=27V 70 60 50 40 30 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, T_A(℃)



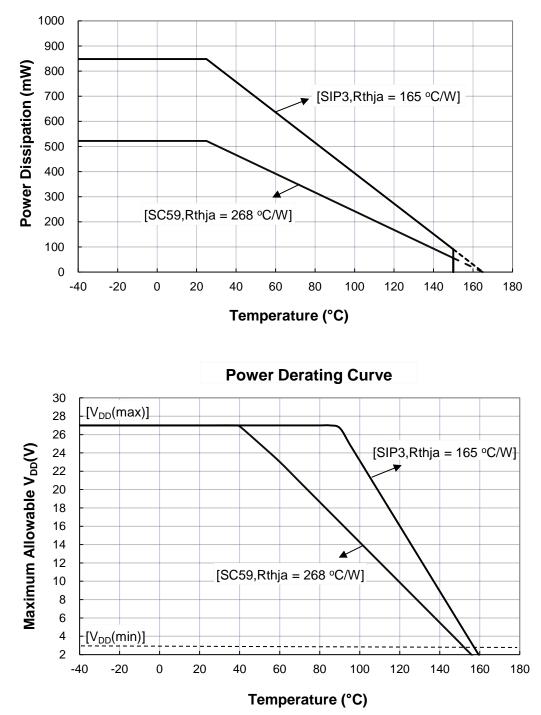
AH3231Q-AH3234Q/AH3270Q-AH3272Q Document number: DS41821 Rev. 5 - 2



Thermal Performance Characteristics

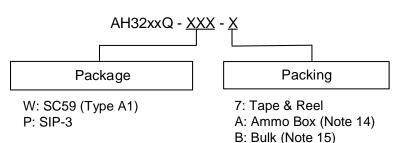
Symbol	Parameter	Conditions	Rating	Unit
R _{0 JA} Package Therma	Backage Thermal Basistance	SC59, 50mm*50mm 2oz MRB PCB, single layer	268	°C/W
	Fackage meimai Resistance	SIP-3, 50mm*50mm 2oz MRB PCB, single layer	143	°C/W

Thermal Derating Curve vs. Ambient Temperature





Ordering Information



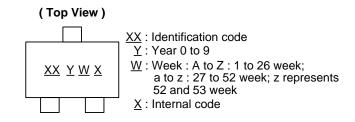
	Package		Bul	k Box	7" Tape and Reel		Ammo Box	
Part Number	Code	Packaging	Quantity	Part Number Suffix	Quantity	Part Number Suffix	Quantity	Part Number Suffix
AH3231Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3231Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3231Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3232Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3232Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3232Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3233Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3233Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3233Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3234Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3234Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3234Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3270Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3270Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3270Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3271Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3271Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3271Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3272Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3272Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3272Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA

 Ammo Box is for SIP-3 (Ammo Pack) Spread Lead.
 Bulk is for SIP-3 (Bulk Pack) Straight Lead. Notes:



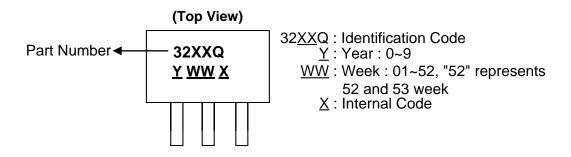
Marking Information

(1) Package Type: SC59 (Type A1)



Part Number	Package	Identification Code
AH3231Q	SC59 (Type A1)	AT
AH3232Q	SC59 (Type A1)	AR
AH3233Q	SC59 (Type A1)	AV
AH3234Q	SC59 (Type A1)	AX
AH3270Q	SC59 (Type A1)	AW
AH3271Q	SC59 (Type A1)	AU
AH3272Q	SC59 (Type A1)	AS

(2) Package Type: SIP-3 (Ammo Pack), SIP-3 (Bulk Pack)



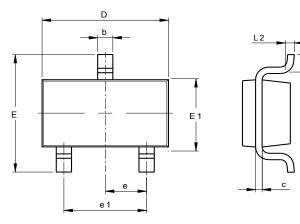
Part Number	Package	Identification Code
AH3231Q	SIP-3 (Ammo Pack)	3231Q
AH3231Q	SIP-3 (Bulk Pack)	3231Q
AH3232Q	SIP-3 (Ammo Pack)	3232Q
AH3232Q	SIP-3 (Bulk Pack)	3232Q
AH3233Q	SIP-3 (Ammo Pack)	3233Q
AH3233Q	SIP-3 (Bulk Pack)	3233Q
AH3234Q	SIP-3 (Ammo Pack)	3234Q
AH3234Q	SIP-3 (Bulk Pack)	3234Q
AH3270Q	SIP-3 (Ammo Pack)	3270Q
AH3270Q	SIP-3 (Bulk Pack)	3270Q
AH3271Q	SIP-3 (Ammo Pack)	3271Q
AH3271Q	SIP-3 (Bulk Pack)	3271Q
AH3272Q	SIP-3 (Ammo Pack)	3272Q
AH3272Q	SIP-3 (Bulk Pack)	3272Q

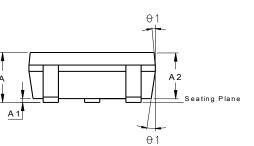


Package Outline Dimensions (All dimensions in mm.)

Please see http://www.diodes.com/package-outlines.html for the latest version.

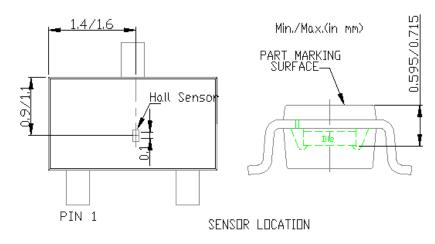
(1) Package Type: SC59 (Type A1)





SC59 (Type A1)						
Dim	Min	Max	Тур			
Α		1.45				
A1	0.00	0.15				
A2	0.90	1.30	1.15			
b	0.30	0.50	-			
Ċ	0.08	0.22				
D		2.90 B	SC			
E		2.80 B	SC			
E1		1.60 B	SC			
е	-	0.95 B	SC			
e1		1.90 B	SC			
L	0.30	0.60	0.45			
L2	0.25 BSC					
θ1	5°	15°	10°			
All	Dimen	sions	in mm			

AH32xxQ Hall sensor

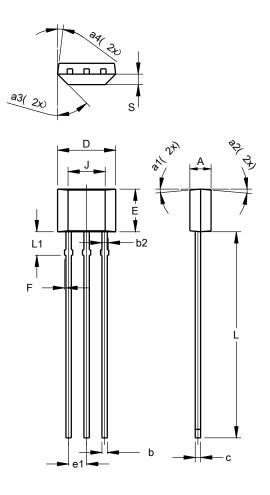




Package Outline Dimensions (continued) (All dimensions in mm.)

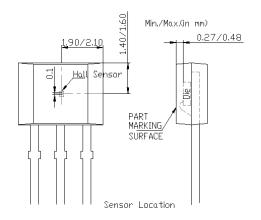
Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SIP-3 (Bulk Pack)



S	IP-3 (Bu	Ik Pack	()
Dim	Min	Max	Тур
Α	1.40	1.60	1.50
b	0.33	0.43	0.38
b2	0.40	0.508	0.46
С	0.35	0.41	0.38
D	3.90	4.30	4.10
Е	2.80	3.20	3.00
e1	1.24	1.30	1.27
F	0.00	0.20	_
J	2	.62 REF	=
L	14.00	15.00	14.50
L1	1.55	1.75	1.65
S	0.63	0.84	0.74
a1	_	_	5°
a2	_		5°
a3	_	_	45°
a4	_	_	3°
All [Dimensi	ons in	mm

AH32xxQ SIP3 Hall sensor

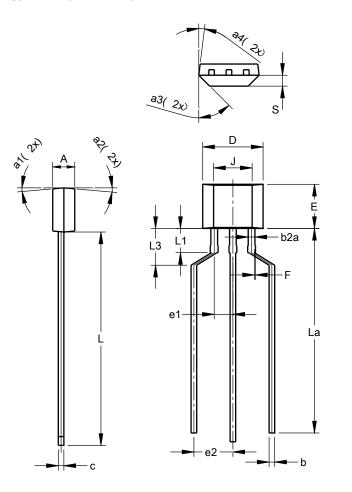




Package Outline Dimensions (continued) (All dimensions in mm.)

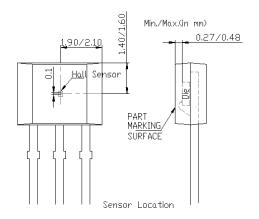
Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) Package Type: SIP-3 (Ammo Pack)



	SIP	0_3	
	(Ammo	-	
Dim	Min	Max	Тур
Α	1.40	1.60	1.50
b	0.33	0.43	0.38
b2a	0.40	0.52	0.46
С	0.35	0.41	0.38
D	3.90	4.30	4.10
Е	2.80	3.20	3.00
e1	1.24	1.30	1.27
e2	2.40	2.90	2.65
F	0.00	0.20	—
J	2	.62 REF	
L	14.00	15.00	14.50
La	12.90	14.90	13.90
L1	1.55	1.75	1.65
L3	2.00	3.00	2.50
S	0.63	0.84	0.74
a1		_	5°
a2	—	—	5°
a3		_	45°
a4		_	3°
All	Dimensi	ons in	mm

AH32xxQ SIP3 Hall sensor



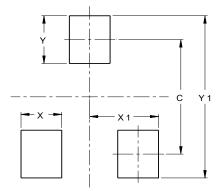
AH3231Q-AH3234Q/AH3270Q-AH3272Q Document number: DS41821 Rev. 5 - 2



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SC59 (Type A1)



Dimensions	Value (in mm)
С	2.40
Х	0.80
X1	1.35
Y	1.00
Y1	3.40



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